Form PTO-1449 Department of Commerce Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	D cket No. **PAT004**	Serial No. **Unassigned**
	Applicants **Wen-Yen Hwang**	
	Filing Date **Herewith**	Group Art Unit **Unassigned**

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JN	5,285,086	02/08/94	Fitzgerald, Jr.			
	5,294,808	03/15/94	Lo			
	5,513,204	04/30/96	Jayaraman			
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	5,981,400	11/09/99	Lo			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	NO

OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

JN	Matthews, J. W. and Blakeslee, A. E., "Defects in Epitaxial Multilayers," *Journal of Crystal Growth 27*, (1974), pp. 118-125.
	Parillaud *et al.*, "High Quality InP on Si by Conformal Growth," *Appl. Phys. Lett. 68*, (1996), p. 2654.
	Lo, Yu-Hwa, "Long Wavelength Vertical Cavity Surface Emitting Lasers," *Hot Topic*, February 1995, p. 20-21.

EXAMINER	JOSEPH NGUYEN	DATE CONSIDERED	10/1/02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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JN	Qian *et al.*, "1.3μm Vertical-Cavity Surface-Emitting Lasers with Double-Bonded GaAs-AlAs Bragg Mirrors," *IEEE Photonics Technology Letters*, Vol. 9, No. 1, January 1997, pp. 8-10.
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EXAMINER	JOSEPH NGUYEN	DATE CONSIDERED	6/1/02

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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)

JN	Salet *et al.*, "Gas-Source Molecular-Beam Epitaxy and Optical Characterisation of Highly-Reflective InGaAsP/InP Multilayer Bragg Mirrors for 1.3μm Vertical-Cavity Lasers," *Electronics Letters.*, Vol. 33, No. 13, June 1997, pp. 1145-1147.
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EXAMINER JOSEPH NGUYEN	DATE CONSIDERED 10/1/02

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